

TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type  
(Four Darlington Power Transistors in One)

## MP4514

### High Power Switching Applications

Hammer Drive, Pulse Motor Drive and Inductive Load Switching

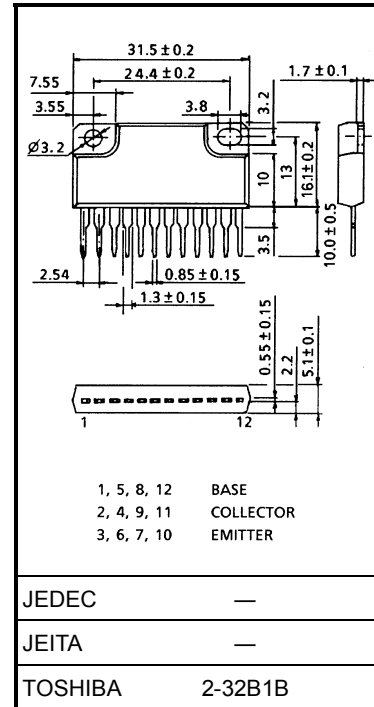
- Package with heat sink isolated to lead (SIP 12 pins)
- High collector power dissipation (4-device operation)  
:  $P_T = 5 \text{ W}$  ( $T_a = 25^\circ\text{C}$ )
- High collector current:  $I_C$  (DC) = 3 A (max)
- High DC current gain:  $h_{FE} = 4000$  (min) ( $V_{CE} = 4 \text{ V}$ ,  $I_C = 1 \text{ A}$ )

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics		Symbol	Rating	Unit
Collector-base voltage		$V_{CBO}$	120	V
Collector-emitter voltage		$V_{CEO}$	100	V
Emitter-base voltage		$V_{EBO}$	6	V
Collector current	DC	$I_C$	3	A
	Pulse	$I_{CP}$	4	
Continuous base current		$I_B$	0.5	A
Collector power dissipation (1-device operation)		$P_C$	3.0	W
Collector power dissipation (4device operation)	$T_a = 25^\circ\text{C}$	$P_T$	5.0	
	$T_c = 25^\circ\text{C}$		25	
Isolation voltage		$V_{\text{Isol}}$	1000	V
Junction temperature		$T_j$	150	$^\circ\text{C}$
Storage temperature range		$T_{\text{stg}}$	-55 to 150	$^\circ\text{C}$

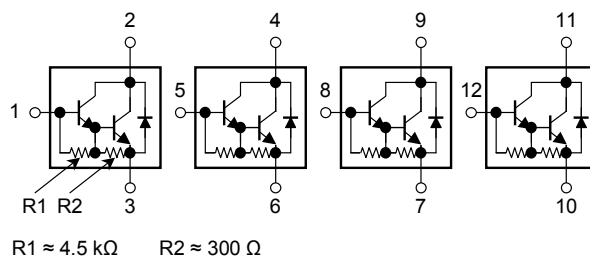
Industrial Applications

Unit: mm

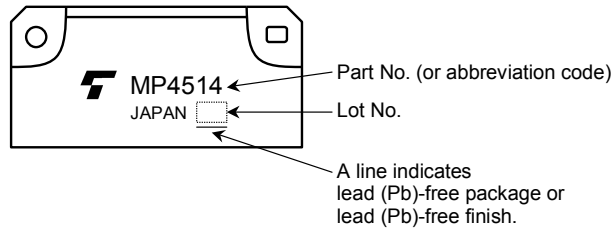


Weight: 6.0 g (typ.)

### Array Configuration



## Marking



## Thermal Characteristics

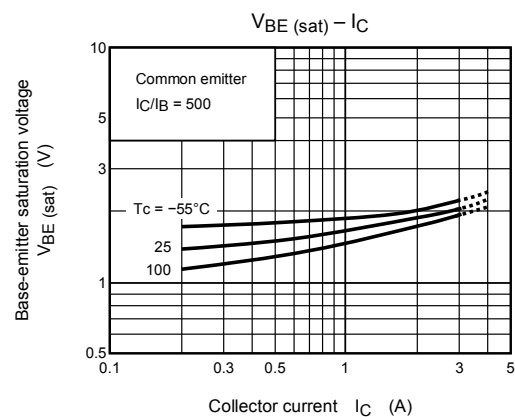
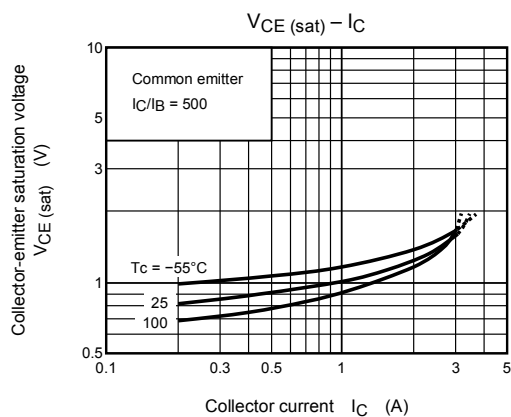
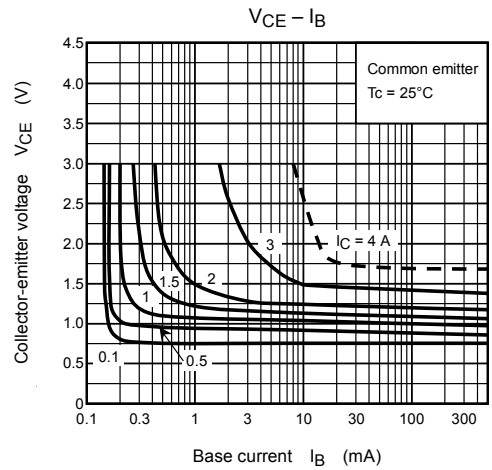
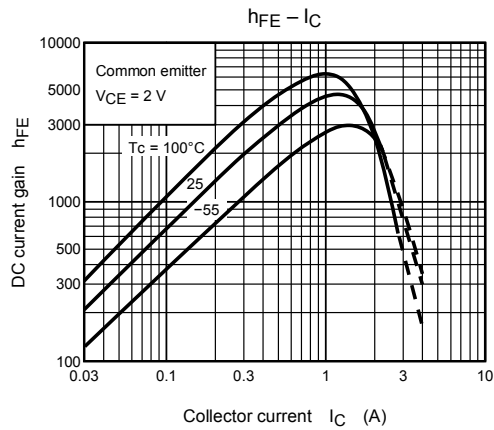
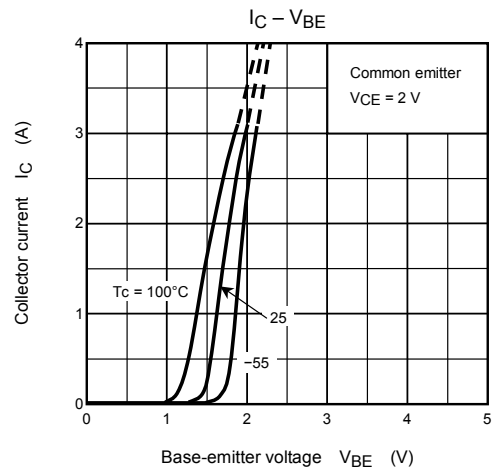
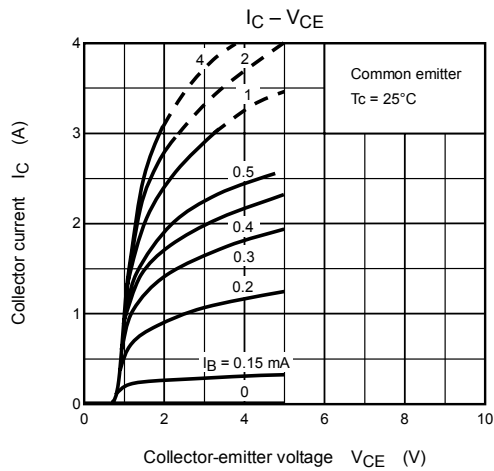
Characteristics	Symbol	Max	Unit
Thermal resistance from channel to ambient (4-device operation, $T_a = 25^\circ\text{C}$ )	$\Sigma R_{th(j-a)}$	25	$^\circ\text{C/W}$
Thermal resistance from channel to case (4-device operation, $T_c = 25^\circ\text{C}$ )	$\Sigma R_{th(j-c)}$	5.0	$^\circ\text{C/W}$
Maximum lead temperature for soldering purposes (3.2 mm from case for 10 second)	$T_L$	260	$^\circ\text{C}$

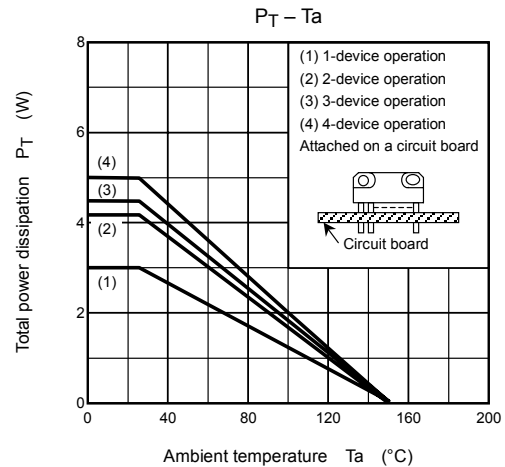
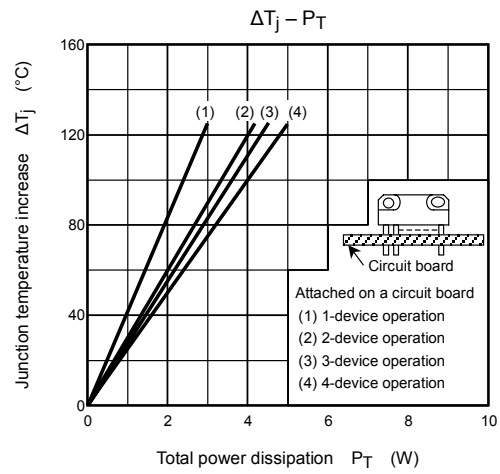
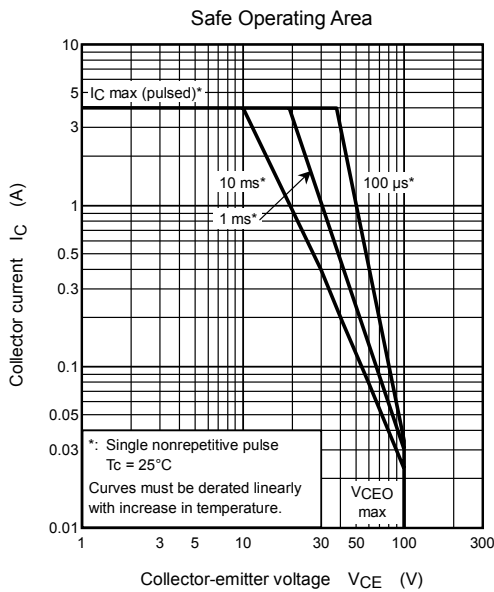
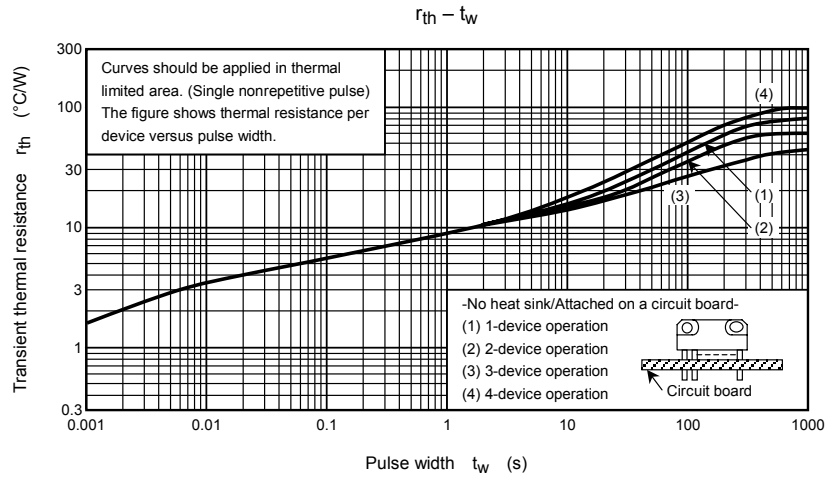
## Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		$I_{CBO}$	$V_{CB} = 120\text{ V}, I_E = 0\text{ A}$	—	—	10	$\mu\text{A}$
Collector cut-off current		$I_{CEO}$	$V_{CE} = 100\text{ V}, I_B = 0\text{ A}$	—	—	10	$\mu\text{A}$
Emitter cut-off current		$I_{EBO}$	$V_{EB} = 6\text{ V}, I_C = 0\text{ A}$	0.5	—	2.5	mA
Collector-base breakdown voltage		$V_{(BR)CBO}$	$I_C = 1\text{ mA}, I_E = 0\text{ A}$	120	—	—	V
Collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0\text{ A}$	100	—	—	V
DC current gain		$h_{FE(1)}$	$V_{CE} = 4\text{ V}, I_C = 1\text{ A}$	4000	—	15000	—
		$h_{FE(2)}$	$V_{CE} = 4\text{ V}, I_C = 2\text{ A}$	1000	—	—	
Saturation voltage	Collector-emitter	$V_{CE(sat)}$	$I_C = 1\text{ A}, I_B = 1\text{ mA}$	—	—	1.5	V
	Base-emitter	$V_{BE(sat)}$	$I_C = 1\text{ A}, I_B = 1\text{ mA}$	—	—	2.0	
Transition frequency		$f_T$	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	—	100	—	MHz
Collector output capacitance		$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0\text{ A}, f = 1\text{ MHz}$	—	20	—	pF
Switching time	Turn-on time	$t_{on}$	<p><math>I_{B1} = -I_{B2} = 1\text{ mA}, \text{duty cycle} \leq 1\%</math></p>	—	0.4	—	$\mu\text{s}$
	Storage time	$t_{stg}$		—	4.0	—	
	Fall time	$t_f$		—	0.6	—	

## Emitter-Collector Diode Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward current	$I_{FM}$	—	—	—	2	A
Surge current	$I_{FSM}$	$t = 1 \text{ s, 1 shot}$	—	—	4	A
Forward voltage	$V_F$	$I_F = 0.5 \text{ A, } I_B = 0 \text{ A}$	—	—	2.0	V
Reverse recovery time	$t_{rr}$	$I_F = 2 \text{ A, } V_{BE} = -3 \text{ V, } dI_F/dt = -50 \text{ A}/\mu\text{s}$	—	1.0	—	$\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		—	5	—	$\mu\text{C}$





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